

74LVC3G04

Triple inverter

Rev. 01 — 4 May 2004

Product data sheet

1. General description

The 74LVC3G04 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC3G04 provides three inverting buffers.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V).
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-B exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V.
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- SOT505-2 and SOT765-1 package
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C.

PHILIPS

3. Quick reference data

Table 1: Quick reference data

$GND = 0\text{ V}$; $T_{amb} = 25\text{ °C}$.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------------|---|--|--------|------|-----|------|
| t_{PHL} , t_{PLH} | propagation delay inputs nA to output nY | $V_{CC} = 1.8\text{ V}$; $C_L = 30\text{ pF}$; $R_L = 1\text{ k}\Omega$ | - | 3.5 | - | ns |
| | | $V_{CC} = 2.5\text{ V}$; $C_L = 30\text{ pF}$; $R_L = 500\ \Omega$ | - | 2.2 | - | ns |
| | | $V_{CC} = 2.7\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\ \Omega$ | - | 2.7 | - | ns |
| | | $V_{CC} = 3.3\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\ \Omega$ | - | 2.7 | - | ns |
| | | $V_{CC} = 5.0\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\ \Omega$ | - | 1.9 | - | ns |
| C_I | input capacitance | | - | 2.5 | - | pF |
| C_{PD} | power dissipation capacitance | $V_{CC} = 3.3\text{ V}$ | [1][2] | 13.5 | - | pF |

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = total load switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

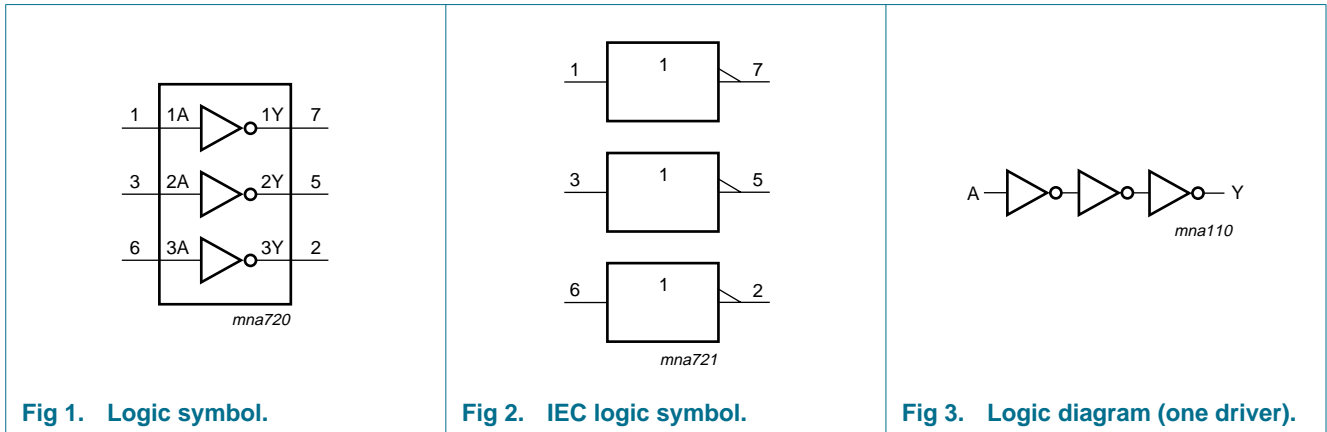
[2] The condition is $V_I = GND$ to V_{CC} .

4. Ordering information

Table 2: Ordering information

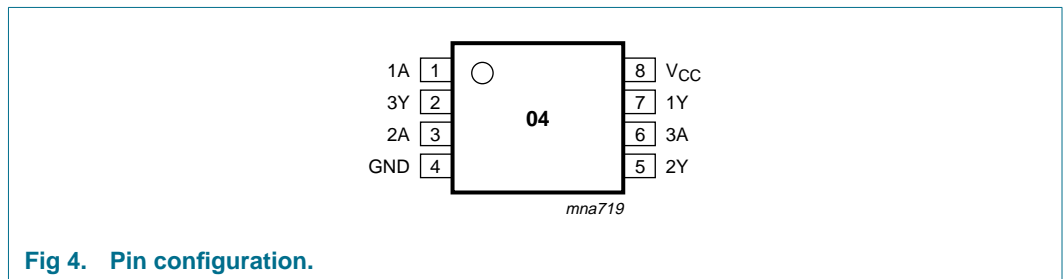
| Type number | Package | | | Version |
|-------------|-------------------|--------|---|----------|
| | Temperature range | Name | Description | |
| 74LVC3G04DP | -40 °C to +125 °C | TSSOP8 | plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm | SOT505-2 |
| 74LVC3G04DC | -40 °C to +125 °C | VSSOP8 | plastic very thin shrink small outline package; 8 leads; body width 2.3 mm | SOT765-1 |

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3: Pin description

| Pin | Symbol | Description |
|-----|-----------------|----------------|
| 1 | 1A | data input |
| 2 | 3Y | data output |
| 3 | 2A | data input |
| 4 | GND | ground (0 V) |
| 5 | 2Y | data output |
| 6 | 3A | data input |
| 7 | 1Y | data output |
| 8 | V _{CC} | supply voltage |

7. Functional description

7.1 Function table

Table 4: Function table [1]

| Input | Output |
|-------|--------|
| nA | nY |
| L | H |
| H | L |

[1] H = HIGH voltage level;
L = LOW voltage level.

8. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------|-------------------------|-------------------------------|-------------|----------------|------|
| V_{CC} | supply voltage | | -0.5 | +6.5 | V |
| I_{IK} | input diode current | $V_I < 0$ V | - | -50 | mA |
| V_I | input voltage | | [1] -0.5 | +6.5 | V |
| I_{OK} | output diode current | $V_O > V_{CC}$ or $V_O < 0$ V | - | ±50 | mA |
| V_O | output voltage | active mode | [1][2] -0.5 | $V_{CC} + 0.5$ | V |
| | | Power-down mode | [1][2] -0.5 | +6.5 | V |
| I_O | output current | $V_O = 0$ V to V_{CC} | - | ±50 | mA |
| I_{CC}, I_{GND} | V_{CC} or GND current | | - | ±100 | mA |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| P_{tot} | power dissipation | $T_{amb} = -40$ °C to +125 °C | - | 300 | mW |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

9. Recommended operating conditions

Table 6: Recommended operating conditions

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------|-------------------------------|------------------------------------|------|-----|----------|------|
| V_{CC} | supply voltage | | 1.65 | - | 5.5 | V |
| V_I | input voltage | | 0 | - | 5.5 | V |
| V_O | output voltage | active mode | 0 | - | V_{CC} | V |
| | | Power-down mode; $V_{CC} = 0$ V | 0 | - | 5.5 | V |
| T_{amb} | operating ambient temperature | | -40 | - | +125 | °C |
| t_r, t_f | input rise and fall times | $V_{CC} = 1.65$ V to 2.7 V | 0 | - | 20 | ns/V |
| | | $V_{CC} = 2.7$ V to 5.5 V | 0 | - | 10 | ns/V |

10. Static characteristics

Table 7: Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--|---|--|----------------------|-----------|----------------------|---------------|
| $T_{amb} = -40\text{ °C to }+85\text{ °C}$ [1] | | | | | | |
| V_{IH} | HIGH-level input voltage | $V_{CC} = 1.65\text{ V to }1.95\text{ V}$ | $0.65 \times V_{CC}$ | - | - | V |
| | | $V_{CC} = 2.3\text{ V to }2.7\text{ V}$ | 1.7 | - | - | V |
| | | $V_{CC} = 2.7\text{ V to }3.6\text{ V}$ | 2.0 | - | - | V |
| | | $V_{CC} = 4.5\text{ V to }5.5\text{ V}$ | $0.7 \times V_{CC}$ | - | - | V |
| V_{IL} | LOW-level input voltage | $V_{CC} = 1.65\text{ V to }1.95\text{ V}$ | - | - | $0.35 \times V_{CC}$ | V |
| | | $V_{CC} = 2.3\text{ V to }2.7\text{ V}$ | - | - | 0.7 | V |
| | | $V_{CC} = 2.7\text{ V to }3.6\text{ V}$ | - | - | 0.8 | V |
| | | $V_{CC} = 4.5\text{ V to }5.5\text{ V}$ | - | - | $0.3 \times V_{CC}$ | V |
| V_{OL} | LOW-level output voltage | $V_I = V_{IH}\text{ or }V_{IL}$ | | | | |
| | | $I_O = 100\text{ }\mu\text{A}; V_{CC} = 1.65\text{ V to }5.5\text{ V}$ | - | - | 0.1 | V |
| | | $I_O = 4\text{ mA}; V_{CC} = 1.65\text{ V}$ | - | - | 0.45 | V |
| | | $I_O = 8\text{ mA}; V_{CC} = 2.3\text{ V}$ | - | - | 0.3 | V |
| | | $I_O = 12\text{ mA}; V_{CC} = 2.7\text{ V}$ | - | - | 0.4 | V |
| | | $I_O = 24\text{ mA}; V_{CC} = 3.0\text{ V}$ | - | - | 0.55 | V |
| | | $I_O = 32\text{ mA}; V_{CC} = 4.5\text{ V}$ | - | - | 0.55 | V |
| V_{OH} | HIGH-level output voltage | $V_I = V_{IH}\text{ or }V_{IL}$ | | | | |
| | | $I_O = -100\text{ }\mu\text{A}; V_{CC} = 1.65\text{ V to }5.5\text{ V}$ | $V_{CC} - 0.1$ | - | - | V |
| | | $I_O = -4\text{ mA}; V_{CC} = 1.65\text{ V}$ | 1.2 | - | - | V |
| | | $I_O = -8\text{ mA}; V_{CC} = 2.3\text{ V}$ | 1.9 | - | - | V |
| | | $I_O = -12\text{ mA}; V_{CC} = 2.7\text{ V}$ | 2.2 | - | - | V |
| | | $I_O = -24\text{ mA}; V_{CC} = 3.0\text{ V}$ | 2.3 | - | - | V |
| | | $I_O = -32\text{ mA}; V_{CC} = 4.5\text{ V}$ | 3.8 | - | - | V |
| I_{LI} | input leakage current | $V_I = 5.5\text{ V or GND}; V_{CC} = 5.5\text{ V}$ | - | ± 0.1 | ± 5 | μA |
| I_{off} | power-off leakage current | $V_I\text{ or }V_O = 5.5\text{ V}; V_{CC} = 0\text{ V}$ | - | ± 0.1 | ± 10 | μA |
| I_{CC} | quiescent supply current | $V_I = V_{CC}\text{ or GND}; I_O = 0\text{ A}; V_{CC} = 5.5\text{ V}$ | - | 0.1 | 10 | μA |
| ΔI_{CC} | additional quiescent supply current per pin | $V_I = V_{CC} - 0.6\text{ V}; I_O = 0\text{ A}; V_{CC} = 2.3\text{ V to }5.5\text{ V}$ | - | 5 | 500 | μA |
| C_I | input capacitance | | - | 2.5 | - | pF |
| $T_{amb} = -40\text{ °C to }+125\text{ °C}$ | | | | | | |
| V_{IH} | HIGH-level input voltage | $V_{CC} = 1.65\text{ V to }1.95\text{ V}$ | $0.65 \times V_{CC}$ | - | - | V |
| | | $V_{CC} = 2.3\text{ V to }2.7\text{ V}$ | 1.7 | - | - | V |
| | | $V_{CC} = 2.7\text{ V to }3.6\text{ V}$ | 2.0 | - | - | V |
| | | $V_{CC} = 4.5\text{ V to }5.5\text{ V}$ | $0.7 \times V_{CC}$ | - | - | V |

Table 7: Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|---|--|-----------------------|-----|------------------------|------|
| V _{IL} | LOW-level input voltage | V _{CC} = 1.65 V to 1.95 V | - | - | 0.35 × V _{CC} | V |
| | | V _{CC} = 2.3 V to 2.7 V | - | - | 0.7 | V |
| | | V _{CC} = 2.7 V to 3.6 V | - | - | 0.8 | V |
| | | V _{CC} = 4.5 V to 5.5 V | - | - | 0.3 × V _{CC} | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V | - | - | 0.1 | V |
| | | I _O = 4 mA; V _{CC} = 1.65 V | - | - | 0.70 | V |
| | | I _O = 8 mA; V _{CC} = 2.3 V | - | - | 0.45 | V |
| | | I _O = 12 mA; V _{CC} = 2.7 V | - | - | 0.60 | V |
| | | I _O = 24 mA; V _{CC} = 3.0 V | - | - | 0.80 | V |
| | | I _O = 32 mA; V _{CC} = 4.5 V | - | - | 0.80 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = -100 μA; V _{CC} = 1.65 V to 5.5 V | V _{CC} - 0.1 | - | - | V |
| | | I _O = -4 mA; V _{CC} = 1.65 V | 0.95 | - | - | V |
| | | I _O = -8 mA; V _{CC} = 2.3 V | 1.7 | - | - | V |
| | | I _O = -12 mA; V _{CC} = 2.7 V | 1.9 | - | - | V |
| | | I _O = -24 mA; V _{CC} = 3.0 V | 2.0 | - | - | V |
| | | I _O = -32 mA; V _{CC} = 4.5 V | 3.4 | - | - | V |
| I _{LI} | input leakage current | V _I = 5.5 V or GND; V _{CC} = 5.5 V | - | - | ±20 | μA |
| I _{off} | power-off leakage current | V _I or V _O = 5.5 V; V _{CC} = 0 V | - | - | ±20 | μA |
| I _{CC} | quiescent supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V | - | - | 40 | μA |
| ΔI _{CC} | additional quiescent supply current per pin | V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V | - | - | 5000 | μA |

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8: Dynamic characteristics

GND = 0 V; for test circuit see [Figure 6](#).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit | |
|---|---|------------------------------------|---------|-----|------|------|----|
| T_{amb} = -40 °C to +85 °C [1] | | | | | | | |
| t _{PHL} , t _{PLH} | propagation delay input nA to output nY | see Figure 5 | | | | | |
| | | V _{CC} = 1.65 V to 1.95 V | 1.0 | 3.5 | 8.0 | ns | |
| | | V _{CC} = 2.3 V to 2.7 V | 0.5 | 2.2 | 4.4 | ns | |
| | | V _{CC} = 2.7 V | 0.5 | 2.7 | 5.2 | ns | |
| | | V _{CC} = 3.0 V to 3.6 V | 0.5 | 2.7 | 4.1 | ns | |
| | | V _{CC} = 4.5 V to 5.5 V | 0.5 | 1.9 | 3.2 | ns | |
| C _{PD} | power dissipation capacitance | V _{CC} = 3.3 V | [2] [3] | - | 13.5 | - | pF |

Table 8: Dynamic characteristics ...continued
 GND = 0 V; for test circuit see [Figure 6](#).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--|---|------------------------------------|-----|-----|-----|------|
| T_{amb} = -40 °C to +125 °C | | | | | | |
| t _{PHL} , t _{PLH} | propagation delay input nA to output nY | see Figure 5 | | | | |
| | | V _{CC} = 1.65 V to 1.95 V | 1.0 | - | 9.5 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 0.5 | - | 5.4 | ns |
| | | V _{CC} = 2.7 V | 0.5 | - | 7.0 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 0.5 | - | 5.5 | ns |
| | | V _{CC} = 4.5 V to 5.5 V | 0.5 | - | 3.8 | ns |

[1] All typical values are measured at nominal V_{CC} and T_{amb} = 25 °C.

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = total load switching outputs;

Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

[3] The condition is V_I = GND to V_{CC}.

12. Waveforms

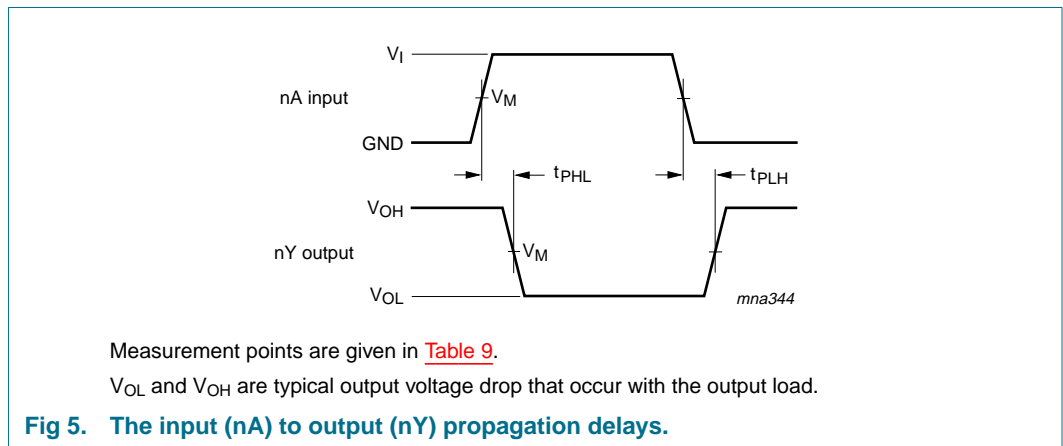


Table 9: Measurement points

| Supply voltage | Input | | Output |
|------------------|-----------------------|-----------------|-----------------------|
| V _{CC} | V _M | V _I | V _M |
| 1.65 V to 1.95 V | 0.5 × V _{CC} | V _{CC} | 0.5 × V _{CC} |
| 2.3 V to 2.7 V | 0.5 × V _{CC} | V _{CC} | 0.5 × V _{CC} |
| 2.7 V | 1.5 V | 2.7 V | 1.5 V |
| 3.0 V to 3.6 V | 1.5 V | 2.7 V | 1.5 V |
| 4.5 V to 5.5 V | 0.5 × V _{CC} | V _{CC} | 0.5 × V _{CC} |

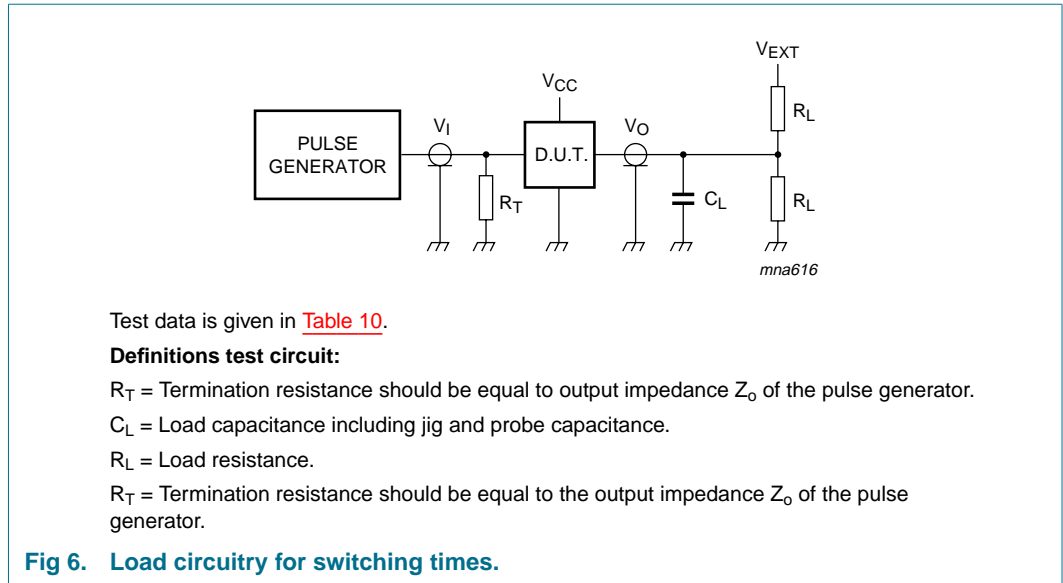


Table 10: Test data

| Supply voltage | Input | | Load | | V_{EXT} | | |
|------------------|----------|---------------|-------|--------------|--------------------|--------------------|--------------------|
| V_{CC} | V_I | $t_r = t_f$ | C_L | R_L | t_{PLH}, t_{PHL} | t_{PZH}, t_{PHZ} | t_{PZL}, t_{PLZ} |
| 1.65 V to 1.95 V | V_{CC} | ≤ 2.0 ns | 30 pF | 1 k Ω | open | GND | $2 \times V_{CC}$ |
| 2.3 V to 2.7 V | V_{CC} | ≤ 2.0 ns | 30 pF | 500 Ω | open | GND | $2 \times V_{CC}$ |
| 2.7 V | 2.7 V | ≤ 2.5 ns | 50 pF | 500 Ω | open | GND | 6 V |
| 3.0 V to 3.6 V | 2.7 V | ≤ 2.5 ns | 50 pF | 500 Ω | open | GND | 6 V |
| 4.5 V to 5.5 V | V_{CC} | ≤ 2.5 ns | 50 pF | 500 Ω | open | GND | $2 \times V_{CC}$ |

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

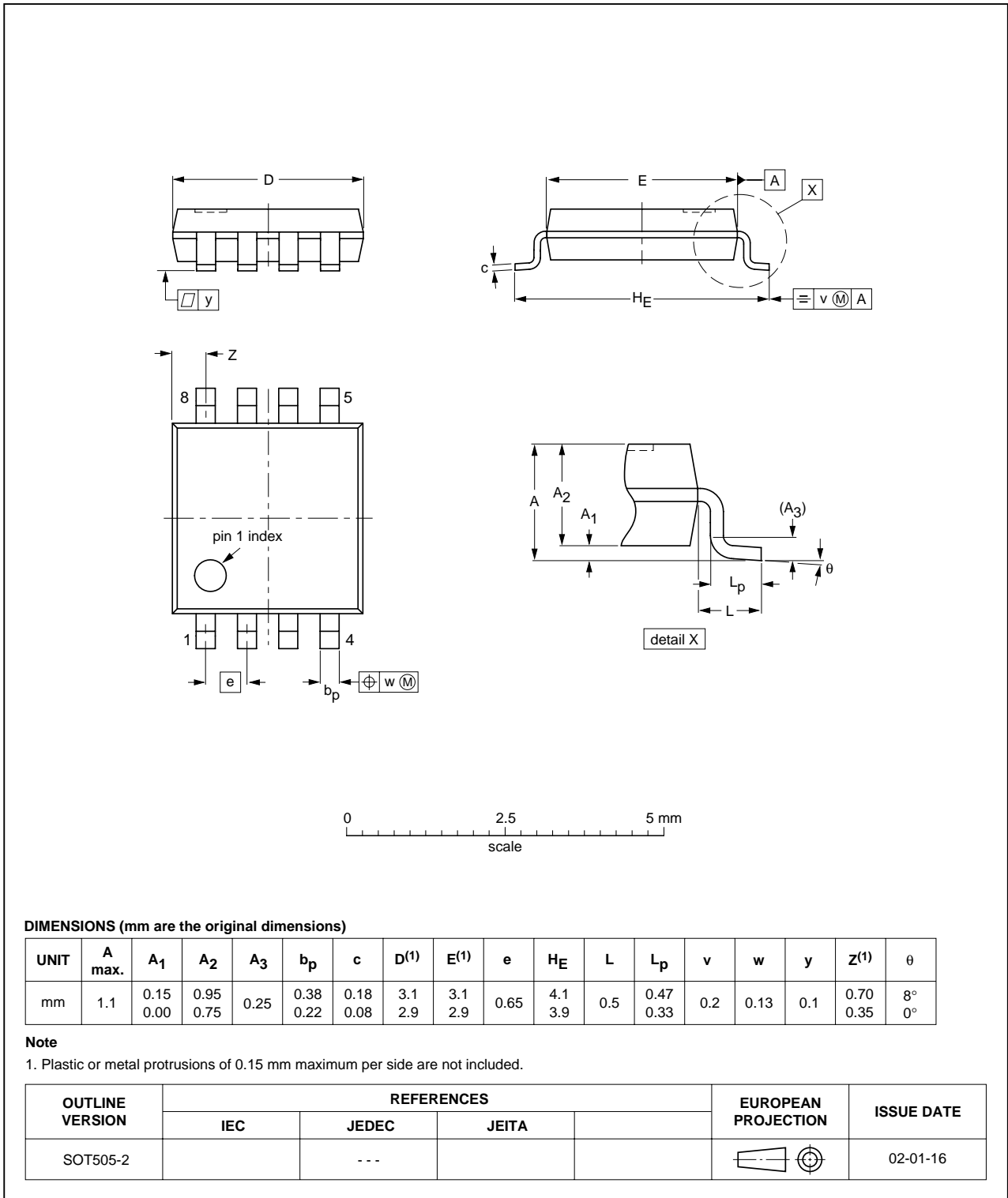


Fig 7. Package outline TSSOP8.

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

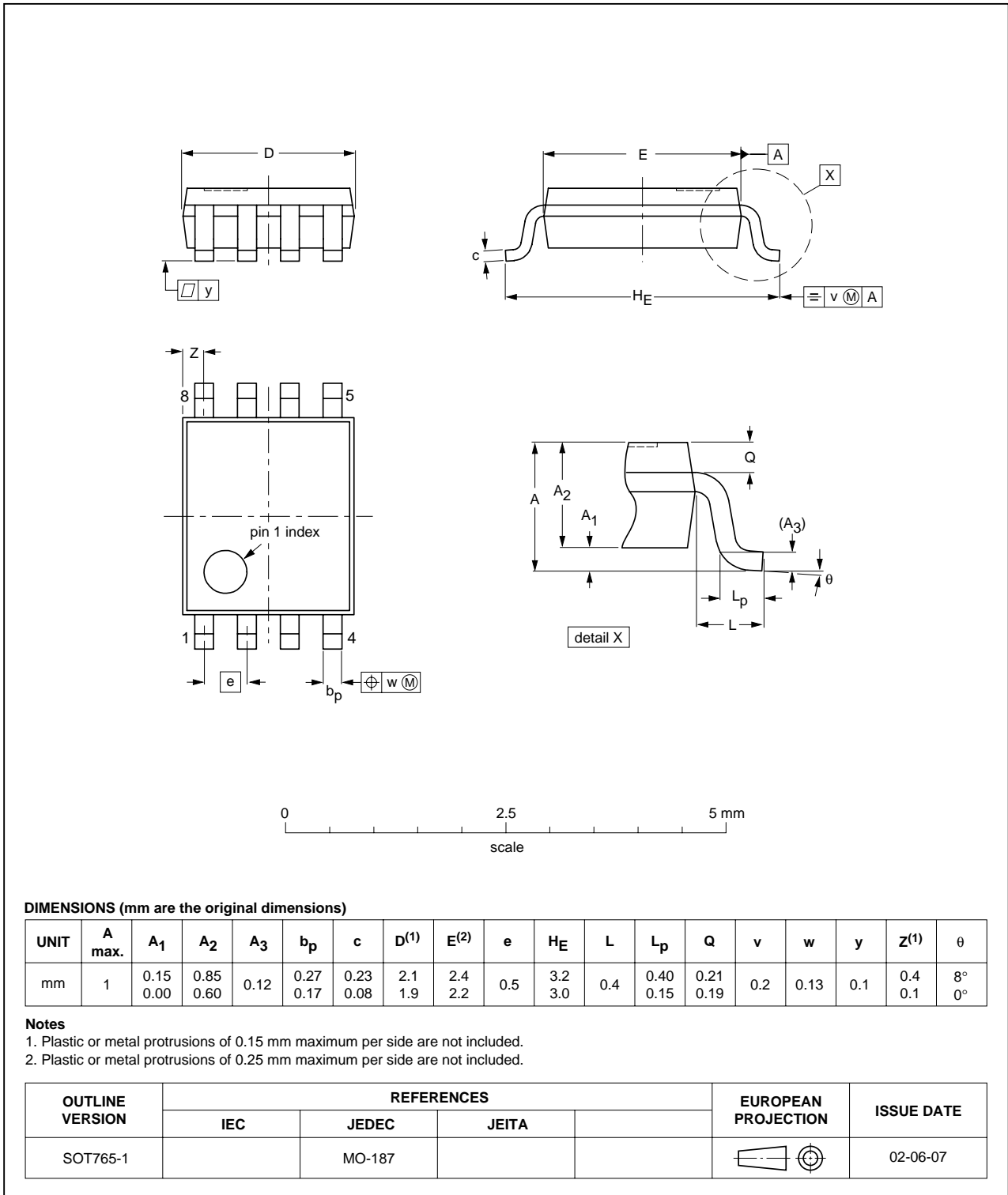


Fig 8. Package outline VSSOP8

14. Revision history

Table 11: Revision history

| Document ID | Release date | Data sheet status | Change notice | Order number | Supersedes |
|-------------|--------------|-------------------|---------------|----------------|------------|
| 74LVC3G04_1 | 20040504 | Product data | - | 9397 750 13075 | - |

15. Data sheet status

| Level | Data sheet status ^[1] | Product status ^[2] ^[3] | Definition |
|-------|----------------------------------|--|--|
| I | Objective data | Development | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice. |
| II | Preliminary data | Qualification | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product. |
| III | Product data | Production | This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). |

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

16. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

17. Disclaimers

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

18. Contact information

For additional information, please visit: <http://www.semiconductors.philips.com>

For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

19. Contents

| | | |
|-----|--|----|
| 1 | General description | 1 |
| 2 | Features | 1 |
| 3 | Quick reference data | 2 |
| 4 | Ordering information | 2 |
| 5 | Functional diagram | 3 |
| 6 | Pinning information | 3 |
| 6.1 | Pinning | 3 |
| 6.2 | Pin description | 3 |
| 7 | Functional description | 4 |
| 7.1 | Function table | 4 |
| 8 | Limiting values | 4 |
| 9 | Recommended operating conditions | 4 |
| 10 | Static characteristics | 5 |
| 11 | Dynamic characteristics | 6 |
| 12 | Waveforms | 7 |
| 13 | Package outline | 9 |
| 14 | Revision history | 11 |
| 15 | Data sheet status | 12 |
| 16 | Definitions | 12 |
| 17 | Disclaimers | 12 |
| 18 | Contact information | 12 |



© Koninklijke Philips Electronics N.V. 2004

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 4 May 2004
Document order number: 9397 750 13075

Published in The Netherlands